## 4-1

## **NEC**

# PNP SILICON TRANSISTOR 2SA733

DESCRIPTION The 2SA733 is designed for use in driver stage of AF amplifier.

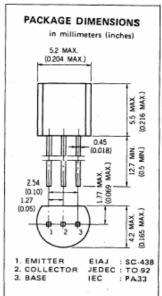
**FEATURES** 

High h<sub>FE</sub> and Excellent Linearity

: 200 TYP.

 $h_{FE}$  (V<sub>CE</sub> = -6.0 V,  $I_{C}$  = -1.0 mA)

#### ABSOLUTE MAXIMUM RATINGS



### ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
hFE	DC Current Gain	90	200	600		V <sub>CE</sub> =-6.0 V, I <sub>C</sub> =-1.0 mA	
NF	Noise Figure		6.0	20	dB	$\dot{V}_{CE}$ =-6.0 V, I <sub>C</sub> =-0.3 mA, R <sub>G</sub> =10 k $\Omega$ , f=100 Hz	
fT	Gain Bandwidth Product	100	180		MHz	V <sub>CE</sub> =-6.0 V, I <sub>E</sub> =10 mA	
Cob	Output Capacitance		4.5	6.0	pF	V <sub>CB</sub> =-10 V, I <sub>E</sub> =0, f=1.0 MHz	
Ісво	Collector Cutoff Current		- ",	-0.1	μА -	V <sub>CB</sub> =-60 V, I <sub>E</sub> =0	
I <sub>EBO</sub>	Emitter Cutoff Current			-0.1	μА	V <sub>EB</sub> =-5.0 V, I <sub>C</sub> =0	
VBE	Base to Emitter Voltage	-0.58	-0.62	-0.68	v	V <sub>CE</sub> =-6.0 V, I <sub>C</sub> =-1.0 mA	
V <sub>CE(sat)</sub>	Collector Saturation Voltage		-0.18	-0.3	V	IC=-100 mA, IB=-10 mA	

Base Current ..... -20 mA

#### Classification of hee

Rank	R	a	Р	K
Range	90 - 180	135 - 270	200 - 400	300 - 600

h<sub>FE</sub> Test Conditions :  $V_{CE} = -6.0 \text{ V}$ ,  $I_{C} = -1.0 \text{ mA}$